



N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected up to 2kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Mechanical Data

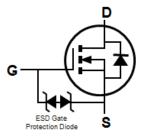
- Package: SOT523
- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Annealed over Alloy 42 Lead-Frame. Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.002 grams (Approximate)

SOT523

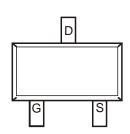




Top View



Equivalent Circuit (Note 5)



Top View

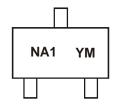
Ordering Information (Note 4)

Part Number	Qualification	Bookaga	Packing		
Fait Number	Qualification	Package	Qty.	Carrier	
DMG1012T-7	Commercial	SOT523	3000	Tape & Reel	
DMG1012T-13	Commercial	SOT523	10000	Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.
- 5. The ESD gate protection diode is only designed to protect against ESD events. No gate-source voltage greater than the maximum V_{GSS} rating (given on page 2) can be applied.

Marking Information



NA1 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: J = 2022) M = Month (ex: 1 = January)

Date Code Key

Downloaded from **Arrow.com**.

Year	2009		2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	W		J	K	L	М	N	0	Р	R	S	T
		-		•								_

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteris	tic		Symbol	Value	Unit
Drain-Source Voltage			VDSS	20	V
Gate-Source Voltage		V _{GSS}	±6	V	
Continuous Drain Current (Note 6)	Steady State	$T_A = +25$ °C $T_A = +85$ °C	lo	0.63 0.45	А
Pulsed Drain Current			IDM	3	Α

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	PD	0.28	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{ heta JA}$	452	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

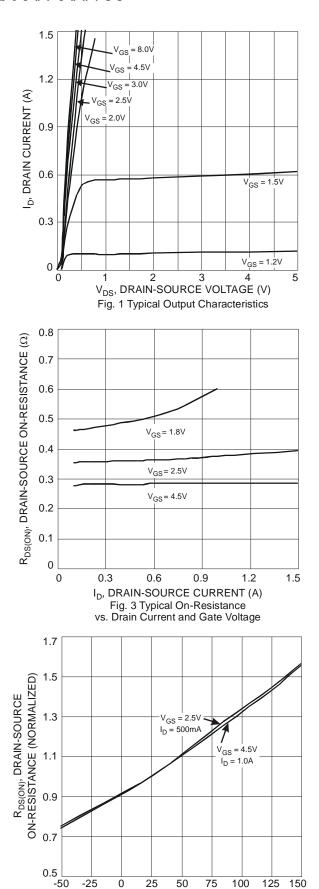
Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

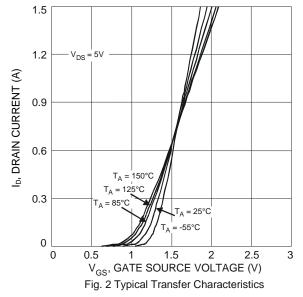
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	_		V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current T _J = +25°C	IDSS	1	_	100	nA	V _{DS} = 20V, V _{GS} = 0V
Gate-Source Leakage	Igss	1	_	±1.0	μA	V _G S = ±4.5V, V _D S = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	Vgs(TH)	0.5	_	1.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
		_	0.3	0.4		$V_{GS} = 4.5V, I_D = 600mA$
Static Drain-Source On-Resistance	R _{DS(ON)}		0.4	0.5	Ω	$V_{GS} = 2.5V, I_D = 500mA$
			0.5	0.7		V _G S = 1.8V, I _D = 350mA
Forward Transfer Admittance	Y _{fs}	1	1.4		S	V _{DS} = 10V, I _D = 400mA
Diode Forward Voltage	VsD	_	0.7	1.2	V	Vgs = 0V, Is = 150mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss	1	60.67	1	pF	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \
Output Capacitance	Coss	1	9.68	1	pF	V _{DS} = 16V, V _{GS} = 0V, f = 1.0MHz
Reverse Transfer Capacitance	Crss	1	5.37	1	pF	1 = 1.01/11/12
Total Gate Charge	Qg	1	736.6	1	рC	151/1/ 101/
Gate-Source Charge	Qgs	1	93.6	1	рC	$V_{GS} = 4.5V, V_{DS} = 10V,$ $I_{D} = 250 \text{mA}$
Gate-Drain Charge	Q_{gd}	1	116.6	1	рC	ID = 230IIIA
Turn-On Delay Time	t _{D(ON)}	_	5.1	_	ns	
Turn-On Rise Time	t _R	1	7.4		ns	$V_{DD} = 10V, V_{GS} = 4.5V,$
Turn-Off Delay Time	tD(OFF)	_	26.7		ns	$R_L = 47\Omega$, $R_G = 10\Omega$, $I_D = 200$ mA
Turn-Off Fall Time	tF	_	12.3	_	ns	10 - 20011# (

Notes:

- 6. Device mounted on FR-4 PCB, with minimum recommended pad layout.7. Short duration pulse test used to minimize self-heating effect.8. Guaranteed by design. Not subject to product testing.







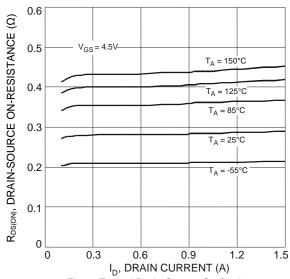


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

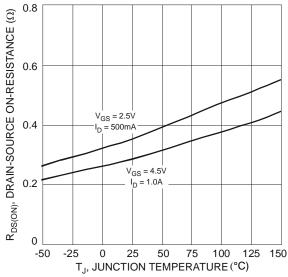


Fig. 6 On-Resistance Variation with Temperature

T_J, JUNCTION TEMPERATURE (°C)

Fig. 5 On-Resistance Variation with Temperature



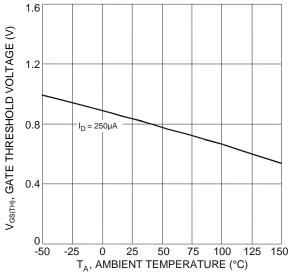
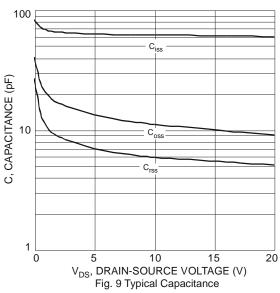


Fig. 7 Gate Threshold Variation vs. Ambient Temperature



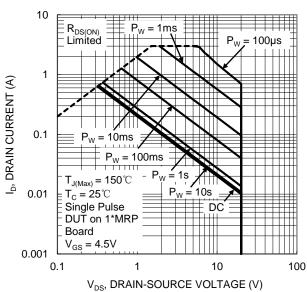


Fig. 11 SOA, Safe Operation Area

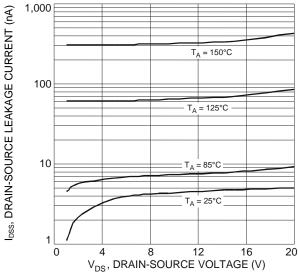
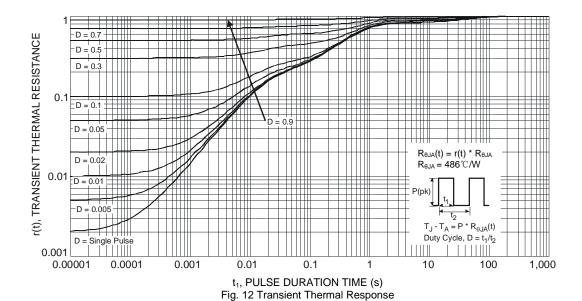


Fig. 10 Typical Drain-Source Leakage Current vs. Drain-Source Voltage



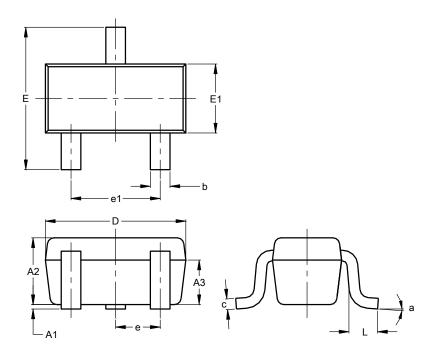




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT523

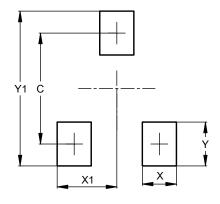


	SC	T523					
Dim	Min	Max	Тур				
A1	0.00	0.10	0.05				
A2	0.60	0.80	0.75				
A3	0.45	0.65	0.50				
b	0.15	0.30	0.22				
C	0.10	0.20	0.12				
D	1.50	1.70	1.60				
Е	1.45	1.75	1.60				
E1	0.75	0.85	0.80				
е		0.50 BS	С				
e1	0.90	1.10	1.00				
L	0.20	0.40	0.33				
а	0°		8°				
All Dimensions in mm							

Suggested Pad Layout

 $\label{prop:lease} Please see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$

SOT523



Dimensions	Value (in mm)
С	1.29
X	0.40
X1	0.70
Y	0.51
V1	1.90



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